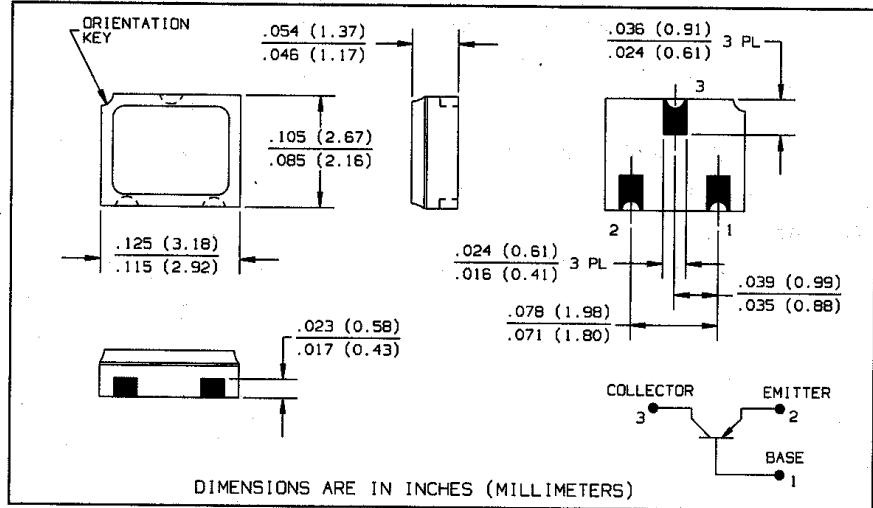
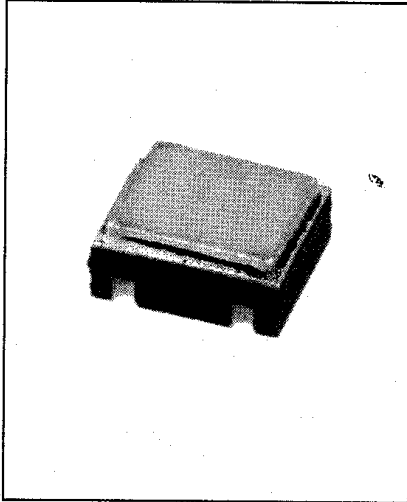


Surface Mount PNP General Purpose Transistor

Type TX, TXV, 2N2907AUB



Features

- Ceramic surface mount package
- Miniature package to minimize circuit board area
- Hermetically sealed
- Footprint and pin-out matches SOT-23 packaged transistors
- Qualification per MIL-PRF-19500/291

Description

The TX/TXV2N2907AUB is a miniature, hermetically sealed, ceramic surface mount general purpose switching transistor. The miniature three pin ceramic package is ideal for upgrading commercial grade circuits to military reliability levels where plastic SOT-23 devices have been used. The "UB" suffix denotes the 3 terminal chip carrier package, type "B" per MIL-PRF-19500/291.

Typical screening and lot acceptance tests are provided on page 13-4. The burn-in condition is $V_{CB} = 30\text{ V}$, $P_D = 200\text{ mW}$, $T_A = 25^\circ\text{ C}$, $t = 80\text{ hrs}$. Refer to MIL-PRF-19500/291 for complete requirements. In addition, the TX and TXV versions receive 100% thermal response testing.

When ordering parts without processing, do not use a JAN prefix.

Absolute Maximum Ratings ($T_A = 25^\circ\text{ C}$ unless otherwise noted)

Collector-Base Voltage	60 V
Collector-Emitter Voltage	60 V
Emitter-Base Voltage	5.0 V
Collector Current-Continuous	600 mA
Operating Junction Temperature (T_J)	-65° C to $+200^\circ\text{ C}$
Storage Junction Temperature (T_{stg})	-65° C to $+200^\circ\text{ C}$
Power Dissipation @ $T_A = 25^\circ\text{ C}$	0.3 W
Power Dissipation @ $T_C = 25^\circ\text{ C}$	1.16 W ⁽¹⁾
Soldering Temperature (vapor phase reflow for 30 sec.)	215° C
Soldering Temperature (heated collet for 5 sec.)	260° C

Notes:

(1) Derate linearly $6.6\text{ mW}/^\circ\text{ C}$ above 25° C .

Types TX, TXV-2N2907AUB

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS	TEST CONDITION
Off Characteristics					
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	60		V	$I_C = 10\ \mu\text{A}, I_E = 0$
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	60		V	$I_C = 10\ \text{mA}, I_B = 0^{(2)}$
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	5.0		V	$I_E = 10\ \mu\text{A}, I_C = 0$
I_{CBO}	Collector-Base Cutoff Current		10	nA	$V_{CB} = 50\ \text{V}, I_E = 0$
			10	μA	$V_{CB} = 50\ \text{V}, I_E = 0, T_A = 150^\circ\text{C}$
I_{CES}	Collector-Emitter Cutoff Current		50	nA	$V_{CE} = 50\ \text{V}$
I_{EBO}	Emitter-Base Cutoff Current		50	nA	$V_{EB} = 4.0\ \text{V}, I_C = 0$
On Characteristics					
h_{FE}	Forward-Current transfer Ratio	75		-	$V_{CE} = 10\ \text{V}, I_C = 0.1\ \text{mA}$
		100	450	-	$V_{CE} = 10\ \text{V}, I_C = 1.0\ \text{mA}$
		100		-	$V_{CE} = 10\ \text{V}, I_C = 10\ \text{mA}$
		100	300	-	$V_{CE} = 10\ \text{V}, I_C = 150\ \text{mA}^{(2)}$
		50		-	$V_{CE} = 10\ \text{V}, I_C = 500\ \text{mA}^{(2)}$
		50		-	$V_{CE} = 10\ \text{V}, I_C = 1.0\ \text{mA}, T_A = -55^\circ\text{C}$
$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage		0.40	V	$I_C = 150\ \text{mA}, I_B = 15\ \text{mA}^{(2)}$
			1.60	V	$I_C = 500\ \text{mA}, I_B = 50\ \text{mA}^{(2)}$
$V_{BE(SAT)}$	Base-Emitter Saturation Voltage		1.30	V	$I_C = 150\ \text{mA}, I_B = 15\ \text{mA}^{(2)}$
			2.60	V	$I_C = 500\ \text{mA}, I_B = 50\ \text{mA}^{(2)}$
Small-Signal Characteristics					
h_{fe}	Forward-Current Transfer Ratio	100		-	$V_{CE} = 10\ \text{V}, I_C = 1.0\ \text{mA}, f = 1.0\ \text{kHz}$
h_{fe1}	Forward-Current Transfer Ratio	2.0		-	$V_{CE} = 20\ \text{V}, I_C = 50\ \text{mA}, f = 100\ \text{MHz}$
C_{obo}	Open Circuit Output Capacitance		8.0	pF	$V_{CB} = 10\ \text{V}, 100\ \text{kHz} \leq f \leq 1.0\ \text{MHz}$
C_{ibo}	Input Capacitance (Output Open)		30	pF	$V_{EB} = 2.0\ \text{V}, 100\ \text{kHz} \leq f \leq 1.0\ \text{MHz}$
Switching Characteristics					
t_{on}	Turn-On Time		45	ns	$V_{CC} = 30\ \text{V}, I_C = 150\ \text{mA}, I_{B1} = 15\ \text{mA}$
t_{off}	Turn-Off Time		300	ns	$V_{CC} = 30\ \text{V}, I_C = 150\ \text{mA}, I_{B1} = I_{B2} = 15\ \text{mA}$

(2) Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$